





SBL560 SCHOTTKY RECTIFIER



Features

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- High Current Capability
- Low Power Loss, High Efficiency
- High Surge Current Capability
- For Use in Low Voltage, High Frequency Inverters,
 Free Wheeling, and Polarity Protection Applications
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Applications

- · Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Disk drives
- Battery charging

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	-	60	V
Average Rectified Forward Current	I _{F (AV)}	50% duty cycle @T _C =105°C, rectangular wave form	5	А
Peak One Cycle Non-Repetitive Surge Current	I _{FSM}	8.3 ms, half Sine pulse, T _C =25°C	120	Α

Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	V _{F1}	@ 5A, Pulse, T _J = 25 °C	0.55	0.60	V
	V _{F2}	@ 5A, Pulse, T _J = 125 °C	0.52	0.55	V
Reverse Current*	I _{R1}	@V _R = Rated V _R , Pulse, T _J = 25 °C	0.09	1.0	mA
	I _{R2}	@V _R = Rated V _R , Pulse, T _J = 125°C	18	40	mA
Junction Capacitance	Ст	@V _R = 5V, T _C = 25 °C f _{SIG} = 1MHz	180	400	pF
Voltage Rate of Change	dv/dt	-	-	10,000	V/us

^{*} Pulse width < 300 μs, duty cycle < 2%



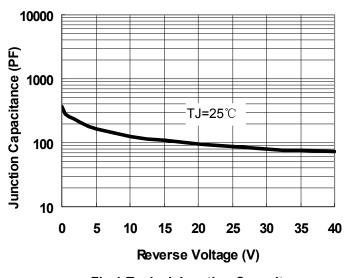




Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +125	°C
Storage Temperature	T _{stg}	-	-55 to +125	°C
Typical Thermal Resistance Junction to Case	R ₀ JC	DC operation	8	°C/W
Approximate Weight	wt	-	1.02	g

Ratings and Characteristics Curves



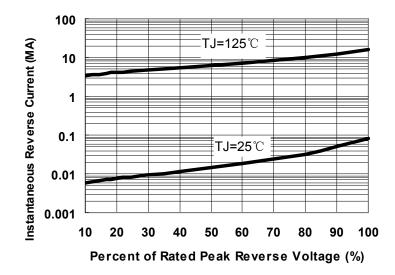


Fig.1-Typical Junction Capacitance

Fig.2-Typical Reverse Current

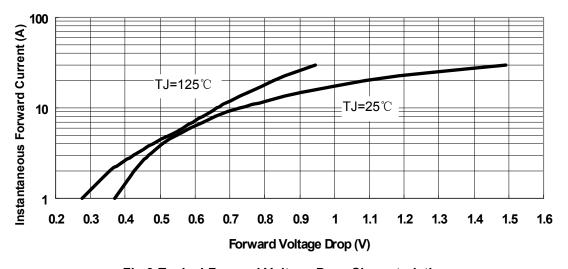


Fig.3-Typical Forward Voltage Drop Characteristics

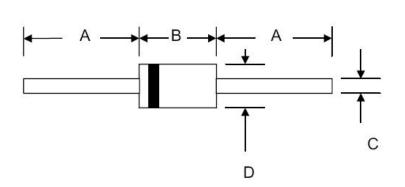
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Mechanical Dimensions DO-201AD



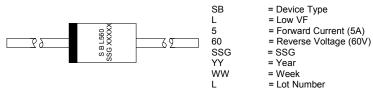
SYMBOL	Millimeters		Inches		
SYMBOL	Min.	Max.	Min.	Max.	
А	25.4	-	1.000	-	
В	8.50	9.50	0.335	0.374	
С	1.2	1.3	0.048	0.052	
D	5.0	5.6	0.197	0.220	

Ordering Information

Device	Package	Shipping	
SBL560	DO-201AD	1250pcs / tape	
SDL300	(Pb-Free)	1230pcs / tape	

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

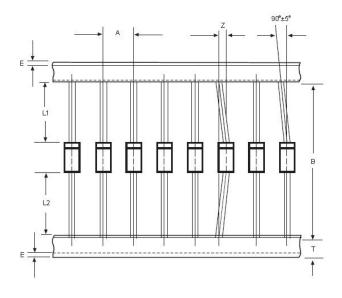
Marking Diagram



Cautions: Molding resin Epoxy resin UL:94V-0

Where XXXXX is YYWWL

Carrier Tape Specification DO-201AD



SYMBOL	Millimeters		
	Min.	Max.	
А	9.50	10.50	
В	50.9	53.9	
Z	-	1.20	
Т	5.60	6.40	
E	-	0.80	
IL1-L2I	-	1.0	

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